

Battery Monitoring IC for Industry

KA49503A Product Standards

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Battery Monitoring IC for Industry

Features

KA49503A is a battery monitoring IC with protection function. With high resolution ADC built-in, KA49503A is capable to measure battery cell voltage and current level accurately.

Through SPI serial interface, microcontroller unit (MCU) is able to read the status and measured result by KA49503A. The ALARM pins alert the MCU with the abnormal condition such as over voltage (OV), under voltage (UV), over current (OC) and short circuit (SC).

KA49503A can support an application with up to 16 batteries cells in series or a maximum voltage of 85V, it is suitable for application with high input voltage such as E-bike, UPS etc.

- Maximum support 16 battery cells in series
- 10mV measurement accuracy with 14 bits voltage ADC for cell voltage, and 5 channels analog input measurement
- Built-in 16 bits low speed current measurement ADC (Coulomb Counter) and high speed current measurement ADC
- Low-side shunt sense resistor for current measurement and monitoring
- 2 interrupt pins ADIRQ1, ADIRQ2 for voltage measurement and current measurement
- Operation mode Active, Standby and Shutdown Mode
- SPI serial communication interface up to 1MHz clock with CRC code correction and watchdog timer
- Built-in ALARM pins for overvoltage, undervoltage, overcurrent and short circuit detection and protection feature
- Built-in cell balancing MOSFET, with support of external cell balance MOSFET operation
- 6 channels General GPIO and 2 channels high voltage output
- High-side Charge (CHG) & Discharge (DIS) N-ch FET driver with built-in charge pump and FETOFF control pin
- 50mA 5V LDO
- Package : LQFP 80L (14x14x1.4mm³, Lead Pitch 0.65mm)

Application

Pedelec, e-Bike, UPS, Server Backup System, Power Tool, Energy Storage Systems etc

Note: This IC may not be able to fulfill the functional safety requirements when Automotive grade Laws or Regulations are applied to Electric Bicycles. In this case, please consider using our Automotive Grade ICs.

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Chapter 1 Overview

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1.1 Recommended Circuit

When connecting a circuit to VDD50, please be careful about below.

- •Adding capacitor more than 1nF to VDD50 pin directly is prohibited.
- ·When needing capacitor more than 1nF, please use through 2Ω resistor.
- Please design as the total capacitor is from 6uF to 16uF.



Note: The recommended circuit is an example. The operation of the mass production set is not guaranteed. Sufficient evaluation and verification is required in the design of the mass production set. Customer is fully responsible for the incorporation of the above illustrated application circuit in the production.

1.2 Electrical Characteristics

1.2.1 ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit	Notes
Supply voltage	V _{VBAT}	-0.3 ~ 99	V	*1
Supply voltage	V _{CVDD}	-0.3 ~ 6.5	V	*1
Operating junction temperature	Τ _i	-40 ~ 125	°C	*2
Storage temperature	T _{stg}	-55 ~ 125	°C	*2
	C16	-0.3 ~ VBAT+1.2	V	*3
	Cn (n=1~15)	-0.3 ~ VBAT+0.3	V	*3
	C0	-0.3 ~ 6.5	V	
	SEN, SCL, SDI, FETOFF STB, GPIOn (n=1~6)	-0.3 ~ V _{CVDD} +0.3	V	*4
Input Voltage Range	TMONIn (n=1∼5),	-0.3 ~ V _{VDD50} +0.3	V	*4
	SRP.SRN	-0.5 ~ 2.0	V	
	VPC	-0.3 ~ 99	V	
	SHDN	-0.3 ~ 6.5	V	
	ALARM1,SDO,NRST	-0.3 ~ V _{CVDD} +0.3	V	
Output Voltage Range	VDD50	-0.3 ~ 6.5	V	
	GPOHn (n=1~2)	-0.3 ~ 99	V	
	ALARM1,SDO,NRST	-6.0 ~ +6.0		*5
Output Current Range	GPIOn (n=1∼6)	(-12.0 ~ +12.0)	mA	*6
Allowable Voltage Between Pins	C _n - C _{n-1} (n=1∼16)	-0.3 ~ 11	V	

Note) This product may sustain permanent damage if subjected to conditions higher than the above stated absolute maximum rating. This rating is the maximum rating and device operating at this range is not guaranteed as it is higher than our stated recommended operating range.

When subjected under the absolute maximum rating for a long time, the reliability of the product may be affected. Do not apply external currents and voltages to any pin not specifically mentioned.

- *1 : The values under the condition not exceeding the above absolute maximum ratings and the power dissipation.
- *2 : Except for the power dissipation, operating ambient temperature, and storage temperature, all ratings are for Ta = 25 °C
- *3 : (VBAT+0.3) & (VBAT+1.2) shall not over 99V.
- *4 : (VCVDD + 0.3), (VVDD50 + 0.3) must not exceed 6.5V.
- *5: + Polarity is the direction that flows from the pin to the outside, polarity is the direction that flows from the outside to the pin.
- *6: This is the rated current at the I / O output drivability setting 2mA. The value of () is the rated current when increasing the I / O output drivability by register settings.

1.2.2 POWER DISSIPATION RATING

Package	θj-а	Өј-с	P _D (Ta=25°C)	P _D (Ta=105°C)
LQFP 80L (14x14x1.4mm ³ , Lead Pitch 0.65mm)	55.5 °C/W	7.2 °C/W	1.80 W	0.36 W

Note) For the actual usage, please refer to the P_D-T_a characteristics diagram in the package specification, follow the power supply voltage, load and ambient temperature conditions to ensure that there is enough margin and the thermal design does not exceed the allowable value.



CAUTION

Although this IC has built-in ESD protection circuit, it may still sustain permanent damage if not handled properly. Therefore, proper ESD precautions are recommended to avoid electrostatic damage to the MOS gates.

1.2.3 RECOMMENDED OPERATING CONDITIONS

Parameter	Pin Name	Min.	Тур.	Max.	Unit	Notes
	V _{VBAT}	12.5	59.2	85	V	
Supply voltage range	V _{CVDD}	3.0	5.0	5.5	V	
	C _n - C _{n-1} (n=1∼16)	0		5.0	V	
	SEN, SCL, SDI	0		V _{CVDD}	V	
	TMONIn (n=1∼5)	0		5.0	V	
Input Voltage Range	GPIOn (n=1∼6)	0		V _{CVDD}	V	
	SRP,SRN	-0.18		0.18	V	
	VPC	0		85	V	
	SHDN	0		V _{VDD50}	V	
Operating Ambient Temperature	Ta _{opr}	-40	25	105	°C	

1.2.4 ELECTRICAL CHARACTERISTICS

at V_{VBAT} = V_{VPACK} = 59.2 V , V_{CVDD} = 5.0V Note: unless otherwise noted, Operating Ambient Temperature is T_a = 25°C±2°C

	Deremeter	Symbol	Condition		Limits		L lucit	Niete	
	Parameter		Condition	Min	Тур	Max	Unit	Note	
s	SUPPLY CURRENT								
	VBAT Active Mode	I _{BAT1}		_	3.1	3.9	mA		
	VBAT Standby Mode	I _{BAT2}	5VLDO:Low Power, Coulomb Counter:off FDRV:Intermittent Communication:off		0.15	0.30	mA		
	VBAT Shutdown Mode	I _{BAT3}		0		1	μA		
5	VLDO								
	VDD50 Output Voltage	V _{VDD}		4.75	5.0	5.25	V		
	VDD50 Drive Current	I _{VDD1}	Normal mode	0		50	mA		
	VDD50 Drive Current	I _{VDD2}	Low Power mode	0		5	mA		
С	ELL BALANCING CONTROL O	UTPUT (CBn)						
	Output Impedance	Z _{CB}	⊿Cn = 3.0V ~ 5.0V	_	12.5	20	Ω		

at V_{VBAT} = V_{VPACK} = 59.2 V , V_{CVDD} = 5.0V Note: unless otherwise noted, Operating Ambient Temperature is $T_a = 25^{\circ}C \pm 2^{\circ}C$

Description				Limits			
Parameter	Symbol	Condition	Min	Тур	Max	Unit	Note
CELL VOLTAGE MONITOR					-		
Input Voltage Range	ΔCn	$C_n - C_{n-1} (n=1 \sim 16)$	0		5	V	
Voltage Resolution	V _{RES}	14bits		0.3		mV	*1
Voltage Accuracy1	V _{ACC_VC1}	ΔCn = 2.0V ~ 4.3 V	-10	_	10	mV	
Voltage Accuracy2	V _{ACC_VC2}	$\Delta Cn = 2.0V \sim 4.3 V$ $Ta = -30^{\circ}C \sim 65^{\circ}C$	-10		10	mV	*2
Conversion Time	t _{conv}	time/cell		50		μS	*1
Cell Measurement Input Current	I _{IN}	Active mode	-5		5	μA	
Input Leakage Current	I _{LK}	Shutdown mode	-1		1	μA	
OVER / UNDER VOLTAGE DET	ECTOR (OV / UV)					
OV detection threshold step	V _{ACC_OV}	2.0~4.5V@6bit		50		mV	*1
UV detection threshold step	V _{ACC_UV}	0.5~3.0V@6bit		50		mV	*1
VPACK CELL VOLTAGE MONI	TOR						
Input Voltage Range	V _{IN}		0		85	V	
Voltage Resolution	V_{RES}	14bits		6.1		mV	*1
Voltage Accuracy1	V _{ACC_} VPACK1	V _{VPACK} = 12.5V ~ 72V	-1		1	V	
Voltage Accuracy2	V _{ACC_} vpack2	$V_{VPACK} = 12.5V \sim 72V$ $T_a = -30^{\circ}C \sim 65^{\circ}C$	-1	_	1	V	*2

*1 : It is a design center value.

*2 It is design value. The inspection is not done.

at V_{VBAT} = V_{VPACK} = 59.2 V , V_{CVDD} = 5.0V Note: unless otherwise noted, Operating Ambient Temperature is T_a = 25°C±2°C

Parameter	Symbo	Condition	Limits			Lloit	Note
Parameter	Ī	Condition	Min	Тур	Max	Unit	note
TMONI1-5 VOLTAGE MONITOR							
Input Voltage Range	V _{IN}		0		5	V	
Voltage Resolution	V _{RES}	14bits	_	0.3		mV	*1
Voltage Accuracy1	V _{ACC} _ TMONI1	VIN = 0.4V~4.7V Not use Pull-up Resistance	-10		10	mV	
Voltage Accuracy2	V _{ACC_} TMONI2	VIN = $0.4V \sim 4.7V$ Not use Pull-up Resistance $T_a = -30^{\circ}C \sim 65^{\circ}C$	-10		10	mV	*3
Input Pull-up Resistance	R _{PU}		7	10	13	kΩ	
Input Pull-up Resistance Temperature coefficient	RT _{PU}	$T_a = -30^{\circ}C \sim 65^{\circ}C$	-1.0		1.0	%	*3
THERMAL SHUTDOWN	THERMAL SHUTDOWN						
Shutdown Threshold	T _{SD2}	Тј	150	175	200	°C	*2 *3

*1 : It is a design center value.

*2 : When thermal shutdown occurs, all circuitry is shutdown.

Following wake up (to active mode) sequence in order to restart.

*3 : It is design value. The inspection is not done.

at V_{VBAT} = V_{VPACK} = 59.2 V , V_{CVDD} = 5.0V Note: unless otherwise noted, Operating Ambient Temperature is T_a = $25^{\circ}C \pm 2^{\circ}C$

Deremeter	Symbo	Condition	Limits			LInit	Note		
Parameter	Ĩ	Condition	Min	Тур	Max	Unit	INOT		
LOW SPEED CURRENT MONI	TOR (SRF	P,SRN)							
Input Voltage Range	V _{IN}		-180		180	mV			
Voltage Resolution	V_{RES}	16bits	_	5.493		μV	*1		
Voltage Accuracy1	V _{ACC} _	VIN = 100mV	-1000	_	1000	μV			
Voltage Accuracy2	V _{ACC} _ IMONI	VIN = 10mV	-150		150	μV	*2		
Voltage Accuracy3	V _{ACC} _	VIN = 1mV	-25	_	25	μV	*2		
HIGH SPEED CURRENT MONITOR (SRP,SRN)									
Input Voltage Range	V _{IN}		-180		180	mV			
Voltage Resolution	V _{RES}	15bits	_	10.99		μV	*1		
Voltage Accuracy1	V _{ACC} _ IMONI	VIN = 100mV	-1000	_	1000	μV			
Voltage Accuracy2	V _{ACC} _ IMONI	VIN = 10mV	-150		150	μV	*2		
Voltage Accuracy3	V _{ACC} _	VIN = 1mV	-50	_	50	μV	*2		
CURRENT PROTECTION (SRF	,SRN)								
Over Current in Charge Detection Accuracy1	V _{CP_OCC}	Detection Threshold 10mV	-5		5	mV	*2		
Over Current in Charge Detection Accuracy2	V _{CP_OCC}	Detection Threshold from 20mV to 100mV	-10	_	10	mV	*2		
Over Current in Charge Detection Accuracy3	V _{CP_OCC}	Detection Threshold from 100mV to 200mV	-10	_	10	%	*2		
Over Current in Discharge Detection Accuracy1	V _{CP_OCD}	Detection Threshold from 25mV to 100mV	-10	_	10	mV	*2		
Over Current in Discharge Detection Accuracy2	V _{CP_OCD}	Detection Threshold from 100mV to 800mV	-10	_	10	%	*2		
Short Circuit in Discharge Detection Accuracy1	V _{CP_SCD}	Detection Threshold from 50mV to 100mV	-10	_	10	mV	*2		
Short Circuit in Discharge Detection Accuracy2	V _{CP_SCD}	Detection Threshold from 100mV to 800mV	-10		10	%	*2		

*1 : It is a design center value.

*2 : It is a design verification value. The inspection is not done.

at V_{VBAT} = V_{VPACK} = 59.2 V , V_{CVDD} = 5.0V Note: unless otherwise noted, Operating Ambient Temperature is T_a = 25°C±2°C

Parameter	Symbol	Condition		Limits			No
Falameter	Symbol	Condition	Min	Тур	Max	Unit	
SENERAL PURPOSE INPUT	ſ/OUTPUT (G	PIO)			1		_
Input Voltage "H"	V _{IH}		V _{CVDD} × 0.8	—	V _{CVDD}	V	
Input Voltage "L"	V _{IL}		0	_	V _{CVDD} ×0.2	V	
Output Voltage "H"	V _{OH}	I _{OH} = -1mA	V _{CVDD} -0.6	_	V _{CVDD} +0.3	V	
Output Voltage "L"	V _{OL}	$I_{OL} = +1mA$	-0.3		0.4	V	
GENERAL PURPOSE HV OU	UTPUT (GPO))					
Output Voltage "L"	V _{OL}	$I_{OL} = +1mA$	-0.3		7.0	V	
DIGITAL INPUT(1) VPC							
Input Voltage "H"	V _{IH}		4.0		_	V	
Input Voltage "L"	V _{IL}		—		0.3	V	
Pull-down resistance	R _{IL}		6	28	55	MΩ	
DIGITAL INPUT(2) SHDN	ł	•				÷	
Input Voltage "H"	V _{IH}		3.0		_	V	
Input Voltage "L"	V _{IL}		—		0.1	V	
Pull-down resistance	R _{IL}		200	820	1500	kΩ	
DIGITAL INPUT(3) SDI,SCL,	SEN,FETOFF	,STB					
Input Voltage "H"	V _{IH}		V _{CVDD} ×0.8	—	V _{CVDD}	V	
Input Voltage "L"	V _{IL}		0		V _{CVDD} ×0.2	V	
Input Leakage Current	I _{LK}		-1	0	1	μΑ	
DIGITAL OUTPUT(1) ALARN	1,SDO						
Output Voltage "H"	V _{OH}	$I_{OH} = -1mA$	V _{CVDD} -0.6	_	V _{CVDD} +0.3	V	
Output Voltage "L"	V _{OL}	I _{OL} = +1mA	-0.3		0.4	V	
DIGITAL OUTPUT(2) NRST							
Output voltage "L"	V _{OL}	I _{OL} = 0 mA	-0.3		0.5	V	
Pull-up resistance	R _{IL}	_	50	100	200	kΩ	

at V_{VBAT} = V_{VPACK} = 59.2 V , V_{CVDD} = 5.0V Note: unless otherwise noted, Operating Ambient Temperature is T_a = $25^{\circ}C \pm 2^{\circ}C$

	Devementer	Currence of	Condition		Limits		1.1	Nata
	Parameter	Symbol	Condition	Min	Тур	Max	Unit	Note
CVI	DD UV							
U	V detection voltage	V _{IL_UV}			2.45		v	*1 *2
U	V release voltage	V _{IH_UV}		_	2.80		V	*1
Ну	ysteresis voltage	V _{HYS_UV}		_	0.35	_	V	*1
VDI	D50 UVLO							
U	VLO detection voltage	V _{IL_UVLO}			4.00		v	*1 *3
Nch	n. FET DRIVER						•	
Dr	rive voltage (DIS="H")	V _{ON_DIS}	$V_{ON_{DIS}} = V_{DIS} - V_{VPACK}$ VGS connect 10M Ω	9	11	13	v	
Dr	rive voltage (CHG="H")	V _{ON_CHG}	$V_{ON_{CHG}} = V_{CHG} - V_{VBAT}$ VGS connect 10M Ω	9	11	13	v	
Dr	rive voltage (DIS="L")	$V_{OFF_{DIS}}$	$V_{OFF_{DIS}} = V_{DIS} - V_{VPACK}$ VGS connect 10M Ω	_	—	0.2	v	
Dr	rive voltage (CHG="L")	V_{OFF_CHG}	$V_{OFF_CHG} = V_{CHG} - V_{VBAT}$ VGS connect 10M Ω	—	_	0.2	V	
Ri	ise time (DIS="L" to "H")	tr	V _{DIS} = 10% to 90% C _L = 47nF		0.8	1.6	ms	
Ri	ise time (CHG="L" to "H")	tr	$V_{CHG} = 10\%$ to 90% $C_{L} = 47nF$		0.8	1.6	ms	
Fa	all time (DIS ="H" to "L")	tf	V _{DIS} = 90% to 10% C _L = 47nF	—	0.5	1.0	ms	
Fa	all time (CHG="H" to "L")	tf	$V_{CHG} = 90\%$ to 10% $C_{L} = 47nF$	_	0.5	1.0	ms	

*1 : It is a design center value.

*2 : When detecting the CVDD UV, CVDD_UV flag (CVDD_STAT: bp2) is set to "0".

*3 : When detecting the VDD50 UVLO, it will be switched to the Shutdown mode. (if VPC pin is "L")

at V_{VBAT} = V_{VPACK} = 59.2 V , V_{CVDD} = 5.0V Note: unless otherwise noted, Operating Ambient Temperature is $T_a = 25^{\circ}C \pm 2^{\circ}C$

Parameter	Symbol	Condition		Limits	1	Linit	Nata		
Parameter	Symbol	Condition	Min	Тур	Max	Unit	Note		
SPI Interface Timing (SEN, SDI, SCL, SDO)									
SCL Frequency	f _{SCL}	_	—	—	1	MHz			
SCL Duty Cycle	t _{DUTY}	_	45	50	55	%			
SEN Rising to SCL Rising	t _{SEN_LD}	—	100	_		ns			
SCL Falling to SEN Falling	t _{SEN_LG}	_	100			ns			
SEN "L" Width	t _{SEN_LO}	_	500	—		ns			
SDI Setup Time	t _{SDI_SU}	SDI valid to SCL falling	100	_		ns			
SDI Hold Time	t _{SDI_HD}	SCL falling to SDI valid	100	_		ns			
SDO Valid Time	t _{SDO_VD}	SCL rising to SDO valid $C_L \leq 50 \text{ pF}$			400	ns			
SDO Disable Time	t _{SDO_DIS}	SEN falling to SDO disable			400	ns			



Fig.2.4.1 SPI Timing



1.3 PIN CONFIGURATION



1.4 PIN FUNCTIONS

Pin No.	Pin name	Туре	Description
1	NC	-	N.C. Pin
2	NC	-	N.C. Pin
3	NC	-	N.C. Pin
4	NC	-	N.C. Pin
5	NC	-	N.C. Pin
6	CVDD	I(Supply)	Digital Voltage Supply
7	SHDN	I	Shutdown Control "L": Active mode / "H": Shutdown mode
8	TMONI1	I	Analog Input Pin 1
9	TMONI2	I	Analog Input Pin 2
10	TMONI3	I	Analog Input Pin 3
11	TMONI4	I	Analog Input Pin 4
12	TMONI5	I	Analog Input Pin 5
13	MODE	I	Test Mode Pin for Manufacturer Use Only (Connect to DVSS always)
14	DVSS	GND	Digital Ground
15	VDD18	0	1.85V LDO Output Pin for Internal Use
16	AVSS1	GND	Analog Ground
17	VDD50R	I	(To be connected to VDD50 pin)
18	VDD50	0	5V Output Pin
19	LDOG	0	Gate Control Pin for 5V LDO NMOS Gate Pin
20	AVSS2	GND	Analog Ground
21	VPC	I	Wake Up Signal Pin "H" Wake Up, Please be always fixed to "L" after Wake Up.
22	VPACK	l(Power Supply)	Positive Pin for Battery Pack
23	DIS	0	Discharge NMOSFET Gate Drive Pin
24	CP1	0	Charge Pump Capacitor Pin (Positive Pin for VPACK)
25	CN1	0	Charge Pump Capacitor Pin (Negative Pin for VPACK)
26	CN2	0	Charge Pump Capacitor Pin (Negative Pin for VBAT)
27	CP2	0	Charge Pump Capacitor Pin (Positive Pin for VBAT)
28	CHG	0	Charge NMOSFET Gate Drive Pin
29	VBATSW	0	Power Pin for 5V LDO NMOS Drain Pin
30	NC	-	N.C. Pin

Pin No.	Pin name	Туре	Description	
31	GPOH2	0	High Voltage General Purpose Output Pin 2 (Open Drain)	
32	GPOH1	0	High Voltage General Purpose Output Pin 1 (Open Drain)	
33	NC	-	N.C. Pin	
34	VBAT	l(Power Supply)	Battery Top Most Pin	
35	C16	I	Cell 16 Input Pin (+ve)	
36	C15	I	Cell 15 Input Pin (+ve) / Cell 16 Input Pin (-ve)	
37	C14	I	Cell 14 Input Pin (+ve) / Cell 15 Input Pin (-ve)	
38	C13	I	Cell 13 Input Pin (+ve) / Cell 14 Input Pin (-ve)	
39	C12	I	Cell 12 Input Pin (+ve) / Cell 13 Input Pin (-ve)	
40	C11	I	Cell 11 Input Pin (+ve) / Cell 12 Input Pin (-ve)	
41	C10	I	Cell 10 Input Pin (+ve) / Cell 11 Input Pin (-ve)	
42	C9	I	Cell 9 Input Pin (+ve) / Cell 10 Input Pin (-ve)	
43	C8	I	Cell 8 Input Pin (+ve) / Cell 9 Input Pin (-ve)	
44	C7	I	Cell 7 Input Pin (+ve) / Cell 8 Input Pin (-ve)	
45	C6	I	Cell 6 Input Pin (+ve) / Cell 7 Input Pin (-ve)	
46	C5	I	Cell 5 Input Pin (+ve) / Cell 6 Input Pin (-ve)	
47	C4	I	Cell 4 Input Pin (+ve) / Cell 5 Input Pin (-ve)	
48	C3	I	Cell 3 Input Pin (+ve) / Cell 4 Input Pin (-ve)	
49	C2	I	Cell 2 Input Pin (+ve) / Cell 3 Input Pin (-ve)	
50	C1	I	Cell 1 Input Pin (+ve) / Cell 2 Input Pin (-ve)	
51	C0	I	Cell 1 Input Pin (-ve)	
52	GND	GND	Analog Ground	
53	SRP	I	Shunt Resistor Positive Pin	
54	NC	-	N.C. Pin	
55	SRN	I	Shunt Resistor Negative Pin	
56	NC	-	N.C. Pin	
57	NC	-	N.C. Pin	
58	NC	-	N.C. Pin	
59	NC	-	N.C. Pin	
60	NC	-	N.C. Pin	

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Pin No.	Pin name	Туре	Description
61	NC	-	N.C. Pin
62	NC	-	N.C. Pin
63	NC	-	N.C. Pin
64	GPIO1	I/O	General Purpose I/O Pin 1
65	GPIO2	I/O	General Purpose I/O Pin 2
66	GPIO3	I/O	General Purpose I/O Pin 3
67	GPIO4/ADIRQ2	I/O	General Purpose I/O Pin 4 / ADIRQ2 Pin
68	GPIO5/ADIRQ1	I/O	General Purpose I/O Pin 5 / ADIRQ1 Pin
69	GPIO6/ALARM2	I/O	General Purpose I/O Pin 6 / ALARM2 Pin
70	ALARM1	0	ALARM1 Pin
71	FETOFF	I	CHG/DIS FET Control Pin - "L" Normal / "H" FET Forced OFF
72	STB	I	Standby Mode Control Pin - "L" Active mode / "H" Standby mode
73	SDO	0	SPI Interface Pin – Data Out
74	SDI	Ι	SPI Interface Pin – Data In
75	SCL	I	SPI Interface Pin – Clock
76	SEN	I	SPI Interface Pin – Enable
77	NRST	0	Power Reset Output Pin (Open Drain)
78	NC	-	N.C. Pin
79	NC	-	N.C. Pin
80	NC	-	N.C. Pin

1.5 FUNCTIONAL BLOCK DIAGRAM



Chapter 2 Battery Connection

The minimum required VBAT pin voltage is 12.5V to guarantee normal operation.

For application using less than 16 cells, all unused cells Cn pins should be connected as shown in figure below, user shall use cells connect to C16, C15, C1 and C2 pins first and follow by battery from lower cell.

Battery cells connection sequence:

Connect the GND pin followed by VBAT pin. After that, it should be connected from the lower cell in turn. GND -> VBAT -> Cell between C0-C1 -> Cell between C1-C2 -> ••••

Figures below show example connection for 15 battery cells and 4 battery cells, please note, it is possible to be connected for 4 battery cells only when the minimum VBAT is higher then 12.5V.







Package Information

LQFP080 14x14mm², Thickness 1.4mm, Lead_Pitch 0.65mm, Lead_Length 1.00mm



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С

DETAIL



VARIATIONS (ALL DIMENSIONS SHOWN IN MM)

SYMBOLS	MIN.	NOM.	MAX.
А	_	_	1.70
A1	0.00	0.10	0.20
A2		1.40REF	
D	15.80	16.00	16.20
D1	13.90	14.00	14.10
E	15.80	16.00	16.20
E 1	13.90	14.00	14.10
L	0.45	0.60	0.75
L1		1.00REF	
Ь	0.25	0.30	0.35
С	0.10	0.15	0.20
е		0.65BSC	
ссс		0.10	
ddd		0.13	
θ	0.0°	_	8.0°

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Important Notice

- 1. When using the IC for new models, verify the safety including the long-term reliability for each product.
- 2. When the application system is designed by using this IC, please confirm the notes in this book.
- Please read the notes to descriptions and the usage notes in the book.
- 3. This IC is intended to be used for general electronic equipment.

Consult our sales staff in advance for information on the following applications: Special applications in which exceptional quality and reliability are required, or if the failure or malfunction of this IC may directly jeopardize life or harm the human body.

Any applications other than the standard applications intended.

- (1) Space appliance (such as artificial satellite, and rocket)
- (2) Traffic control equipment (such as automobile, transportation vehicle such as automobile, airplane, train, and ship)
- (3) Medical equipment for life support
- (4) Submarine transponder
- (5) Control equipment for power plant
- (6) Disaster prevention and security device
- (7) Weapon
- (8) Others : Applications of which reliability equivalent to (1) to (7) is required

Our company shall not be held responsible for any damage incurred as a result of or in connection with the IC being used for any special application, unless our company agrees to the use of such special application. However, for the IC which we designate as products for automotive use, it is possible to be used for automotive.

- 4. This IC is neither designed nor intended for use in automotive applications or environments unless the IC is designated by our company to be used in automotive applications. Our company shall not be held responsible for any damage incurred by customers or any third party as a result of or in connection with the IC being used in automotive application, unless our company agrees to such application in this book.
- 5. Please use this IC in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Our company shall not be held responsible for any damage incurred as a result of our IC being used by our customers, not complying with the applicable laws and regulations.
- 6. Pay attention to the direction of the IC. When mounting it in the wrong direction onto the PCB (printed-circuitboard),

it might be damaged.

- 7. Pay attention in the PCB (printed-circuit-board) pattern layout in order to prevent damage due to short circuit between pins.
 - In addition, refer to the Pin Description for the pin configuration.
- 8. Perform visual inspection on the PCB before applying power, otherwise damage might happen due to problems such as solder-bridge between the pins of the IC. Also, perform full technical verification on the assembly quality, because the same damage possibly can happen due to conductive substances, such as solder ball, that adhere to the IC during transportation.
- 9. Take notice in the use of this IC that it might be damaged when an abnormal state occurs such as output pin-VCC short (Power supply fault), output pin-GND short (Ground fault), or output-to-output-pin short (load short). Safety measures such as installation of fuses are recommended because the extent of the above-mentioned damage will depend on the current capability of the power supply.
- 10. This IC may be changed in order to improve the performance without notice, please make sure the latest specification is used before your final design.

Revision History

Date	Revision	Description
2021.1.28	1.00	1. initially issued.

KA49503A Product Standards

Important Notice

Nuvoton Products are neither intended nor warranted for usage in systems or equipment, any malfunction or failure of which may cause loss of human life, bodily injury or severe property damage. Such applications are deemed, "Insecure Usage".

Insecure usage includes, but is not limited to: equipment for surgical implementation, atomic energy control instruments, airplane or spaceship instruments, the control or operation of dynamic, brake or safety systems designed for vehicular use, traffic signal instruments, all types of safety devices, and other applications intended to support or sustain life.

All Insecure Usage shall be made at customer's risk, and in the event that third parties lay claims to Nuvoton as a result of customer's Insecure Usage, customer shall indemnify the damages and liabilities thus incurred by Nuvoton.

Please note that all data and specifications are subject to change without notice.

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